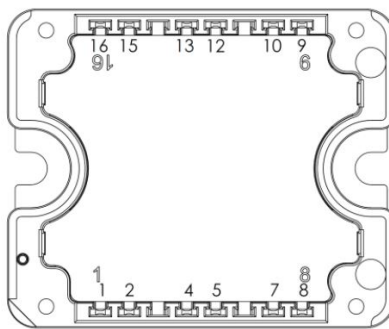
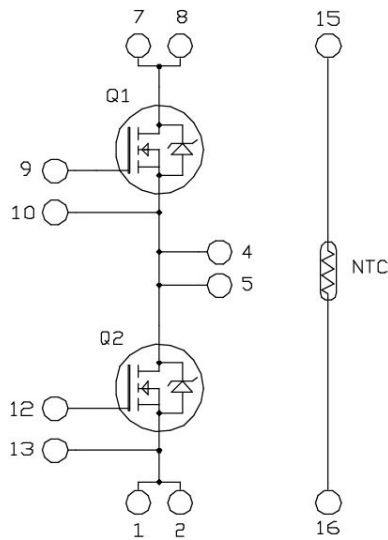


Phase Leg SiC MOSFET Power Module

Product Overview

The MSCSM70AM19T1AG device is a full bridge 700V, 124A silicon carbide (SiC) power module.



Notes:

- Pins 1/2; 4/5; 7/8 must be shorted together.
- All ratings at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified.



These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM70AM19T1AG device:

- SiC Power MOSFET
 - High speed switching
 - Low $R_{DS(on)}$
 - Ultra low loss
- Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AlN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM70AM19T1AG device:

- High efficiency converter
- Outstanding performance at high frequency operation
- Solderable terminals both for power and signal for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS compliant

Application

The MSCSM70AM19T1AG device is designed for the following applications:

- Welding converters
- Switched mode power supplies
- Uninterruptible power supplies
- EV motor and traction drive

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM70AM19T1AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM70AM19T1AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Maximum Ratings	Unit
V_{DSS}	Drain-Source voltage	700	V
I_D	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	124 ¹
		$T_C = 80\text{ }^\circ\text{C}$	98 ¹
I_{DM}	Pulsed drain current	250	
V_{GS}	Gate-Source voltage	-10/23	V
$R_{DS(on)}$	Drain-Source ON resistance	19	m Ω
P_D	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	365

Note:

1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM70AM19T1AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit	
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0V$ $V_{DS} = 700V$	—	—	100	μA	
$R_{DS(on)}$	Drain-Source on resistance	$V_{GS} = 20V$ $I_D = 40A$	$T_J = 25\text{ }^\circ\text{C}$	—	15	19	m Ω
			$T_J = 175\text{ }^\circ\text{C}$	—	18.8	—	
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 4\text{ mA}$	1.9	2.4	—	V	
I_{GSS}	Gate-Source leakage current	$V_{GS} = 20V; V_{DS} = 0V$	—	—	150	nA	

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Electrical Specifications

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM70AM19T1AG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit	
C_{iss}	Input capacitance	$V_{GS} = 0V$	—	4500	—	pF	
C_{oss}	Output capacitance	$V_{DS} = 700V$	—	510	—		
C_{rss}	Reverse transfer capacitance	$f = 1\text{ MHz}$	—	29	—		
Q_g	Total gate charge	$V_{GS} = -5V/20V$	—	215	—	nC	
Q_{gs}	Gate-Source charge	$V_{Bus} = 470V$	—	58	—		
Q_{gd}	Gate-Drain charge	$I_D = 40A$	—	35	—		
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5V/20V$	$T_J = 150^\circ\text{C}$	—	40	—	ns
T_r	Rise time	$V_{Bus} = 400V$		—	40	—	
$T_{d(off)}$	Turn-off delay time	$I_D = 80A$		—	50	—	
T_f	Fall time	$R_{G(on)} = 68\Omega$ $R_{G(off)} = 4.7\Omega$		—	20	—	
E_{on}	Turn-on energy	$V_{GS} = -5V/20V$	$T_J = 150^\circ\text{C}$	—	893	—	μJ
E_{off}	Turn-off energy	$V_{Bus} = 400V$ $I_D = 80A$ $R_{G(on)} = 68\Omega$ $R_{G(off)} = 4.7\Omega$	$T_J = 150^\circ\text{C}$	—	194	—	
R_{Gint}	Internal gate resistance		—	0.69	—	Ω	
R_{thJC}	Junction-to-case thermal resistance		—	—	0.41	$^\circ\text{C/W}$	

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM70AM19T1AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 40A$	—	3.4	—	V
		$V_{GS} = -5V; I_{SD} = 40A$	—	3.8	—	
t_{rr}	Reverse recovery time	$I_{SD} = 40A; V_{GS} = -5V$	—	38	—	ns
Q_{rr}	Reverse recovery charge	$V_R = 400V; di_F/dt = 1000\text{ A}/\mu\text{s}$	—	318	—	nC
I_{rr}	Reverse recovery current		—	14.8	—	A

1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM70AM19T1AG device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristics	Min	Max	Unit		
V _{ISOL}	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz	4000	—	V		
T _J	Operating junction temperature range	−40	175	°C		
T _{JOP}	Recommended junction temperature under switching conditions	−40	T _{Jmax} −25			
T _{STG}	Storage temperature range	−40	125			
T _C	Operating case temperature	−40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight	—	80			g

The following table lists the temperature sensor NTC of the MSCSM70AM19T1AG device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance at 25°C	—	50	—	kΩ
ΔR ₂₅ /R ₂₅	—	—	5	—	%
B _{25/85}	T ₂₅ = 298.15 K	—	3952	—	K
ΔB/B	—	T _C = 100 °C	4	—	%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Note: See [APT0406—Using NTC Temperature Sensor Integrated into Power Module](#) for more information.

1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM70AM19T1AG device.

Figure 1-1. Maximum Thermal Impedance

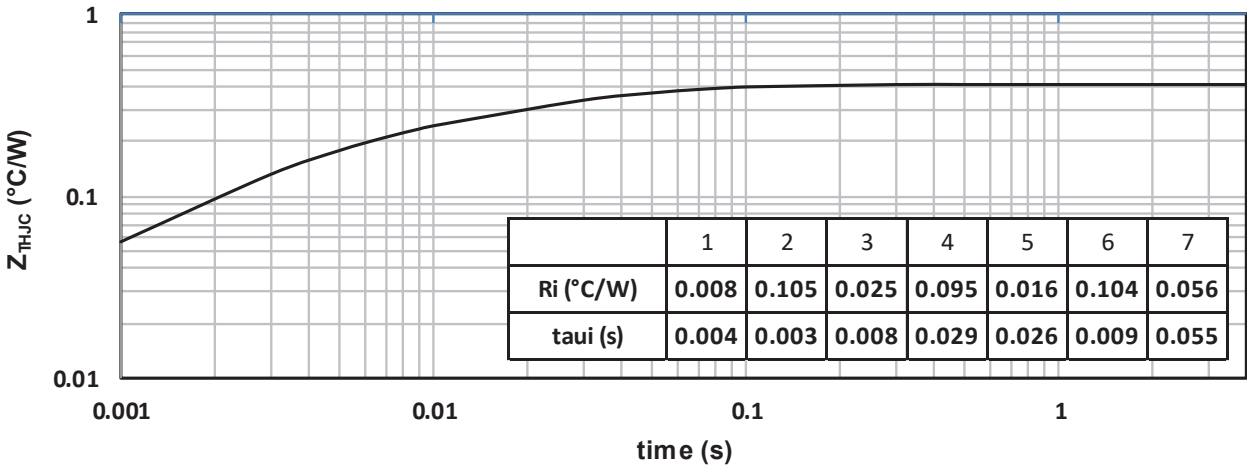


Figure 1-2. Output Characteristics, $T_J = 25^\circ\text{C}$

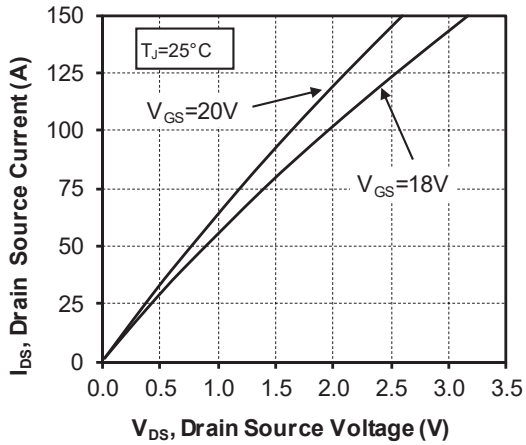


Figure 1-3. Output Characteristics, $T_J = 175^\circ\text{C}$

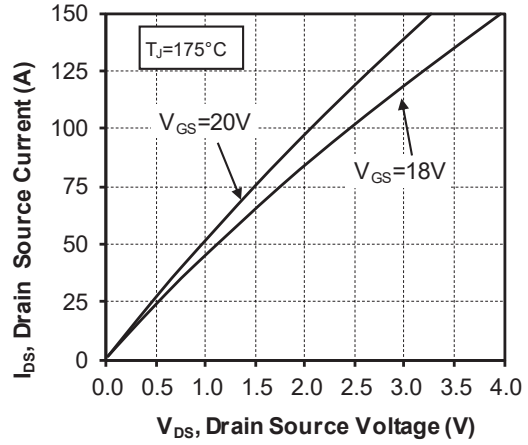


Figure 1-4. Normalized $R_{DS(on)}$ vs. Temperature

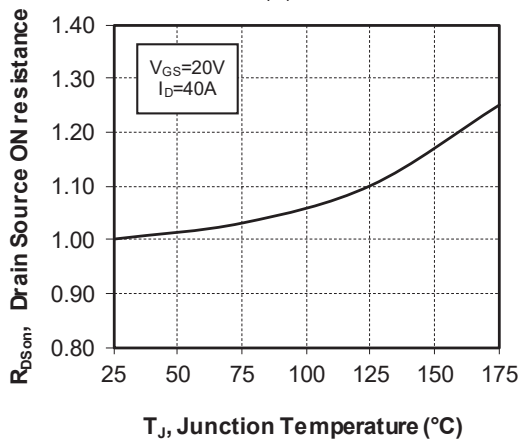


Figure 1-5. Transfer Characteristics

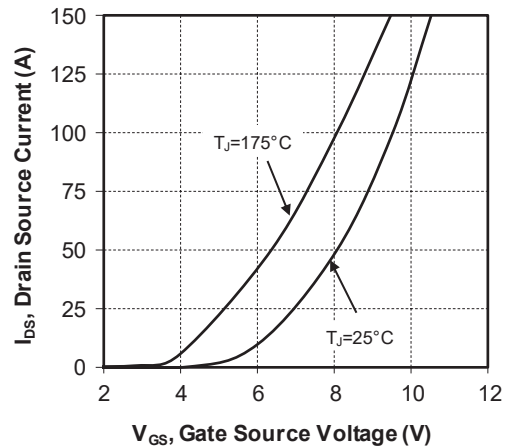


Figure 1-6. Switching Energy vs. Current

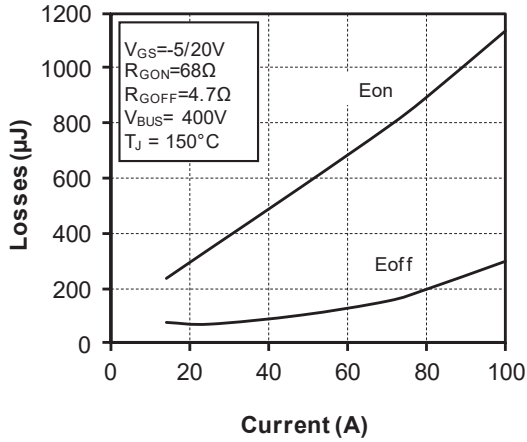


Figure 1-7. Turn On Energy vs. R_g

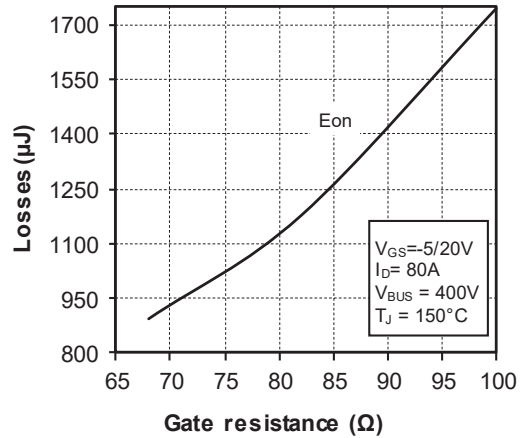


Figure 1-8. Capacitance vs. Drain Source Voltage

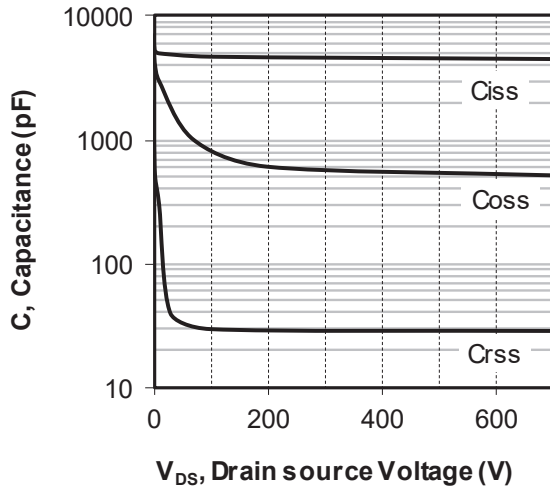


Figure 1-9. Gate Charge vs. Gate Source Voltage

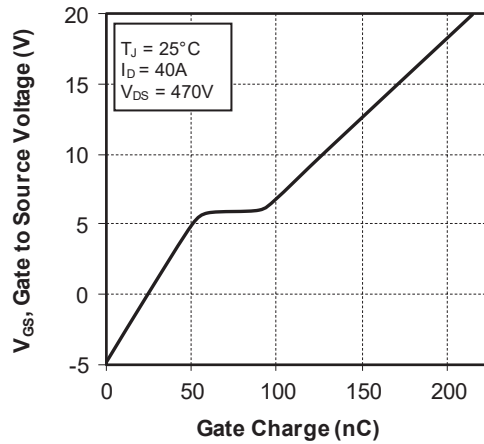


Figure 1-10. Body Diode Characteristics, $T_J = 25^\circ\text{C}$

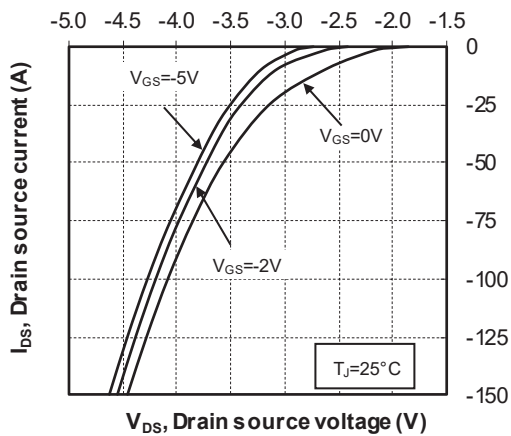
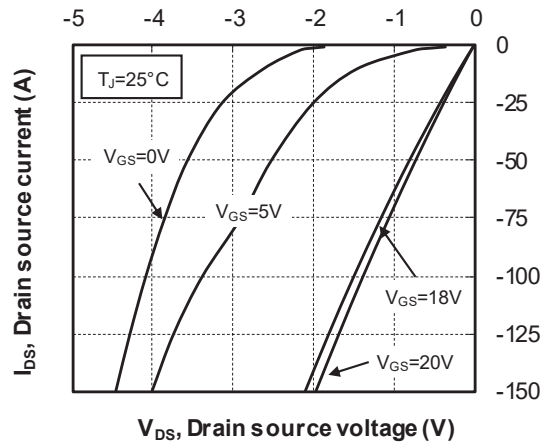


Figure 1-11. 3rd Quadrant Characteristics, $T_J = 25^\circ\text{C}$



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Figure 1-12. Body Diode Characteristics, $T_J = 175^\circ\text{C}$

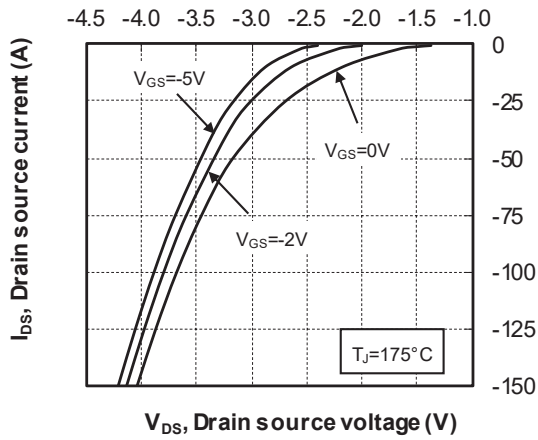


Figure 1-13. 3rd Quadrant Characteristics, $T_J = 175^\circ\text{C}$

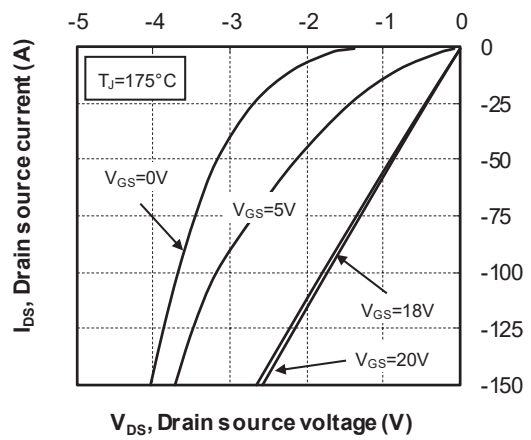


Figure 1-14. Operating Frequency vs Drain Current

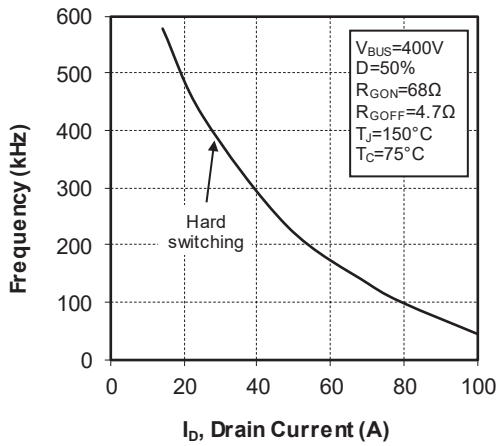
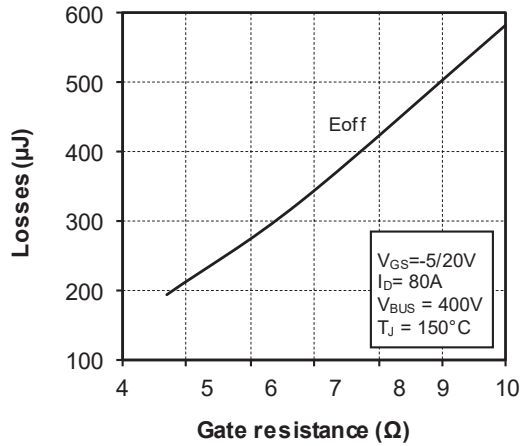


Figure 1-15. Turn Off Energy vs. Rg



3. Revision History

Revision	Date	Description
A	06/2022	Initial Revision

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